



GaAs MMIC SPDT NON-REFLECTIVE SWITCH, DC - 18 GHz

Features

High Isolation: >65 dB up to 6 GHz

>50 dB up to 18 GHz

Low Insertion Loss: 2 dB @ 8 GHz

2.8 dB @ 12 GHz

Fast Switching: 3 ns Rise/Fall Times

Non-Reflective Design

Hermetically Sealed Module

Field Replaceable SMA connectors

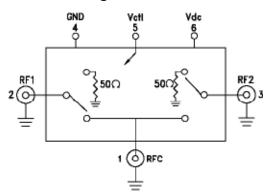
-55 to +85 °C Operating Temperature

Typical Applications

The HMC-C058 is ideal for:

- Fiber Optics & Broadband Telecom
- Microwave Radio & VSAT
- Military Radios, Radar, & ECM
- Test Instrumentation

Functional Diagram



General Description

The HMC-C058 is a general purpose broadband high isolation non-reflective GaAs MESFET SPDT switch housed in a miniature hermetic module with field replaceable SMA connectors. Covering DC to 18 GHz, the switch offers high isolation and low insertion loss. The switch features >65 dB isolation up to 6 GHz and >50 dB isolation up to 18 GHz. A CMOS interface allows a single +5V bias voltage at very low DC currents.

Electrical Specifications, $T_{\Delta} = +25^{\circ}$ C, With Vdc = +5V & 0/+5V Control, 50 Ohm System

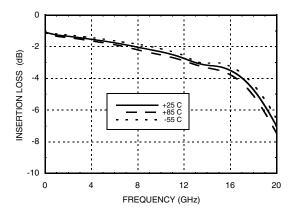
Parameter		Frequency	Min.	Тур.	Max.	Units
Insertion Loss		DC - 6 GHz DC - 10 GHz DC - 18 GHz		1.6 2.0 3.0	2.4 2.8 5.5	dB dB dB
Isolation		DC - 6 GHz DC - 10 GHz DC - 18 GHz	55 50 42	65 60 55		dB dB dB
Return Loss	"On State"	DC - 6 GHz DC - 18 GHz		17 12		dB dB
Return Loss RF1, RF2	"Off State"	DC - 6 GHz DC - 18 GHz		14 17		dB dB
Input Power for 1 dB Compression		0.5 - 18 GHz	24	27		dBm
Input Third Order Intercept (Two-Tone Input Power= +7 dBm Ea	ach Tone)	0.5 - 18 GHz		46		dBm
Switching Characteristics tRISE, tFALL (10/90% RF) tON, tOFF (50% CTL to 10/90% RF)	DC - 18 GHz		3 12		ns ns
Switching Transients		DC - 18 GHz		12		mVpp



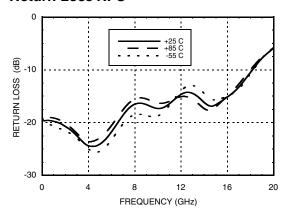
RoHS√

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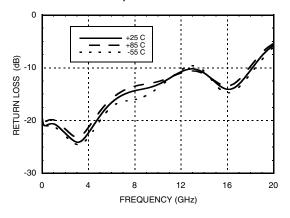
Insertion Loss



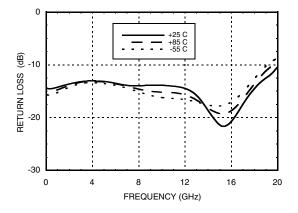
Return Loss RFC



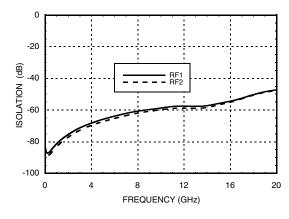
Return Loss RF1, RF2 On



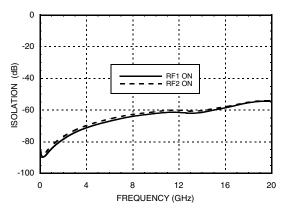
Return Loss RF1, RF2 Off



Isolations



Isolation Between Ports RF1 and RF2

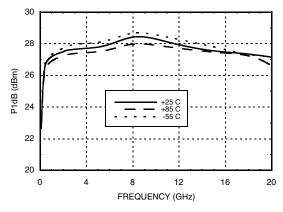




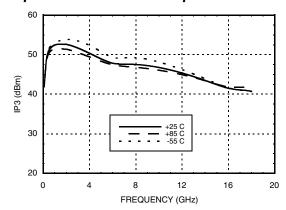


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Input P1dB Compression Point



Input Third Order Intercept Point



Absolute Maximum Ratings

RF Input Power	+30 dBm
Supply Voltage (Vdc)	+7 V
Control Voltage Range (Vctl)	-0.5V to Vdc +0.5V
Hot Switch Power Level	+27 dBm
Storage Temperature	-65 to +150 °C
Operating Temperature	-55 to +85 °C



Control Voltages

State	Bias Condition	
High	+3.5 to Vdc @ 1 mA Typ.	
Low	0 to +1.5V @ 20 μA Typ.	

Truth Table

Control Input	Signal Path State		
VctI	RFC to RF1	RFC to RF2	
High	On	Off	
Low	Off	On	

Bias Voltage & Current

Vdc Range = +5 Vdc ± 10%		
Vdc (V)	ldc (Typ.) (mA)	
+5.0	1.4	

(Bias current increases with switching rate to 15 - 20 mA.)





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Pin Descriptions

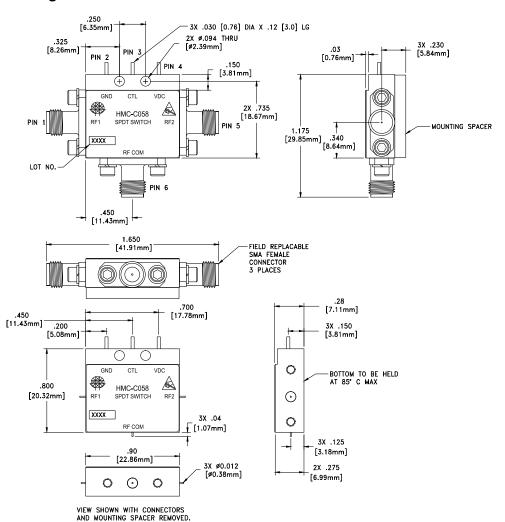
Pin Number	Function	Description	Interface Schematic
1, 2, 3	RFC, RF1, RF2	RF connector, SMA female, field replaceable. These pins are DC coupled and matched to 50 Ohms. DC blocking capacitors are required if external RF line potential is not equal to 0V.	RFC,RF1,RF20—
4	GND	Power supply ground.	= O GNG
5	VetI	CMOS interface, control voltages per table. Requires active pullup to +5V (V _{dc}).	VCTL O SV Zener 4700 -5V (Internal)
6	Vdc	Supply voltage	





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Outline Drawing



Package Information

Package Type C-14

NOTES:

- 1. PACKAGE, LEADS, COVER MATERIAL: KOVAR ™
- PLATING: ELECTROLYTIC GOLD 50 MICROINCHES MIN., OVER ELECTROLYTIC NICKEL 75 MICROINCHES MIN.
- 3. SPACER MATERIAL: NICKEL PLATED ALUMINUM
- 4. DIMENSIONS ARE IN INCHES [MILLIMETERS].
- 5. TOLERANCES ± 0.010 [0.25] UNLESS OTHERWISE SPECIFIED
- 6. FIELD REPLACEABLE SMA CONNECTORS. TENSOLITE 5602-5CCSF OR EQUIVALENT.





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ANALOGDEVICES

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Notes:

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